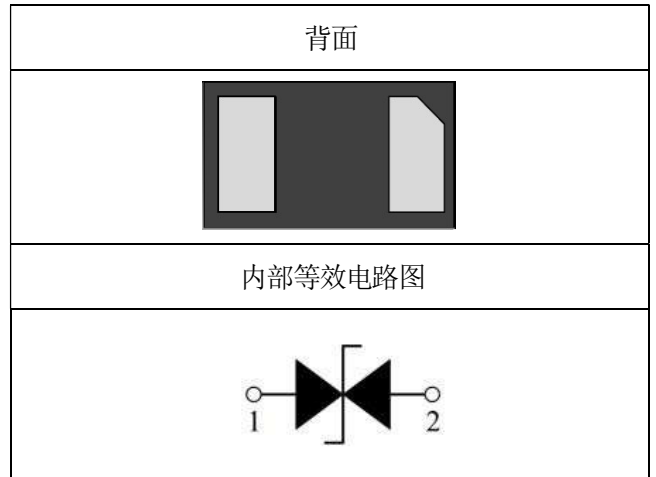


1. 概述和特点

ESD8D3.3C 是利用先进的硅电路工艺生产的双向低电容静电放电保护器件，主要用于电路元件快速过电保护，封装形式为 DFN1006

- 快速的响应时间
- 低箝位电压
- 低漏电电流 (<100nA)
- 低电容
- 适合于高速数据传输线的ESD 保护：
IEC61000-4-2 (ESD)，±30kV (空气放电)；±30kV (接触放电)
- 并联使用
- 封装外型：DFN1006

- 典型参数



$P_{PK}=80W$
$V_{RWM}=3.3V$
$V_C@I_{PP}=8.0A) \leq 10V$
$I_{PP}=8.0A$
$C_j=15pF$

2. 电特性

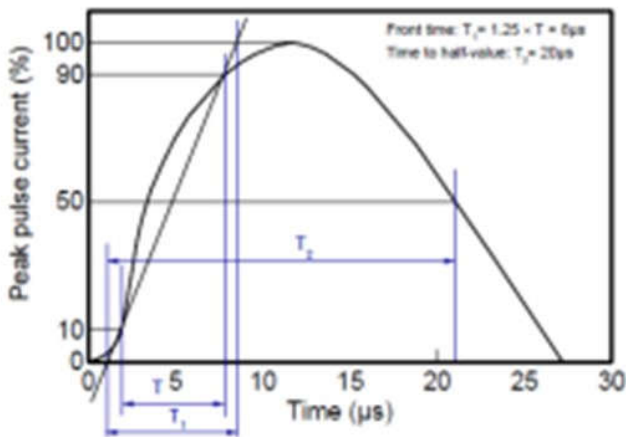
极限参数 ($T_a=25^\circ C$)

参数	Symbol	Rating	Unit
最大峰值功率(8/20us)	P_{PK}	80	W
最大峰值脉冲电流 (8/20us)	I_{PP}	8.0	A
最高工作温度范围	T_{OP}	-55 ~ +150	$^\circ C$
最高存储温度范围	T_{STG}	-55 ~ +150	$^\circ C$

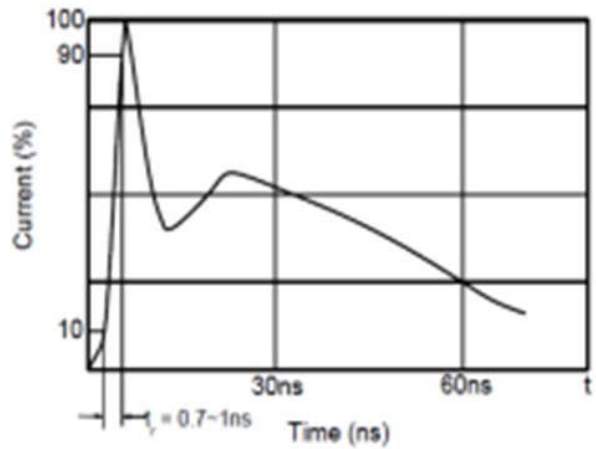
常规参数 ($T_a=25^\circ C$)

参数	Symbol	Test Conditions	Criterion			Unit
			Min	Typ	Max	
维持电压	V_{RWM}				3.3	V
击穿电压	V_{BR}	$I_t=1mA$	3.5	4.1	5	V
漏电流	I_R	$V_{RWM}=\pm 3.3V$			0.1	μA
钳位电压	V_C	$I_{pp}=1A, tp=8/20us$			6.5	V
钳位电压	V_C	$I_{pp}=8A, tp=8/20us$			10	V
电容	C_j	$V_R=0V, f=1Mz$		15	20	pF

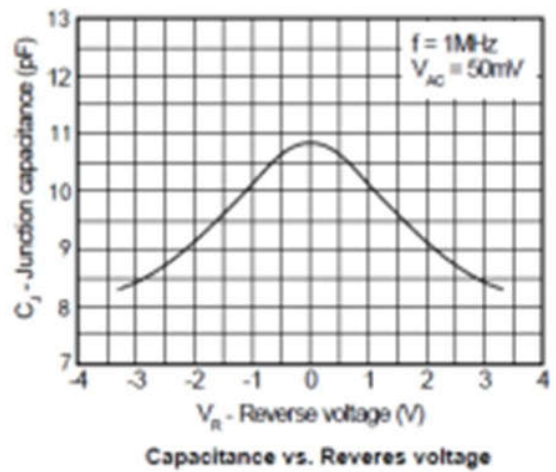
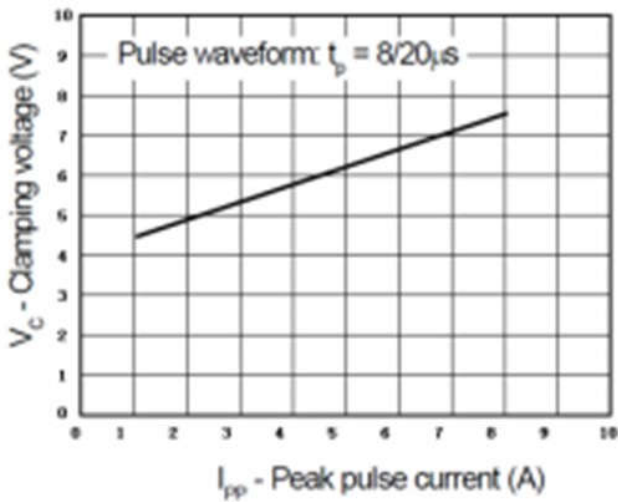
3. 特征曲线



8/20 μs waveform per IEC61000-4-5



Contact discharge current waveform per IEC61000-4-2



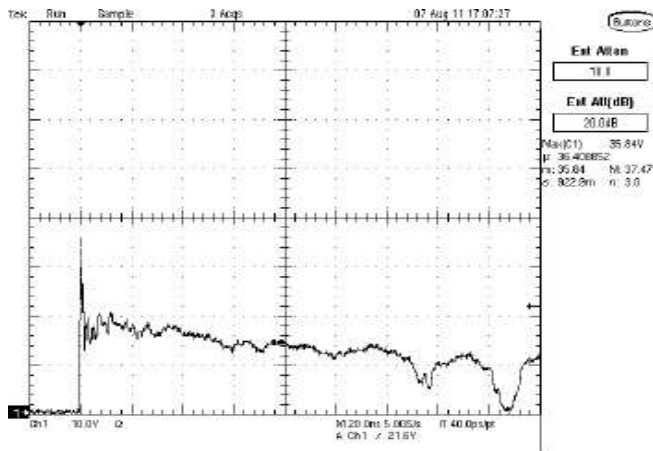


Fig1. ESD Clamping Voltage Screenshot Positive 8 kV Contact per IEC61000-4-2

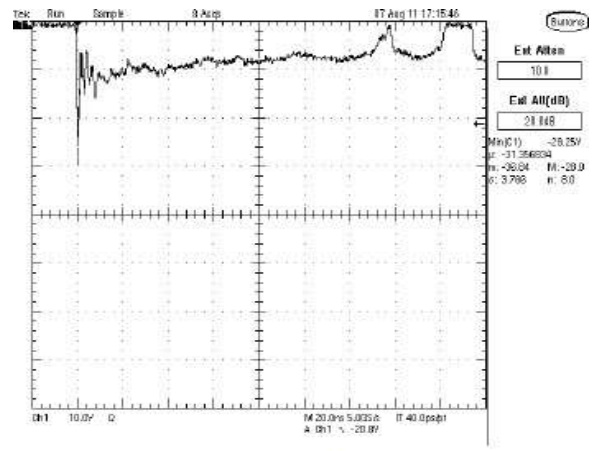
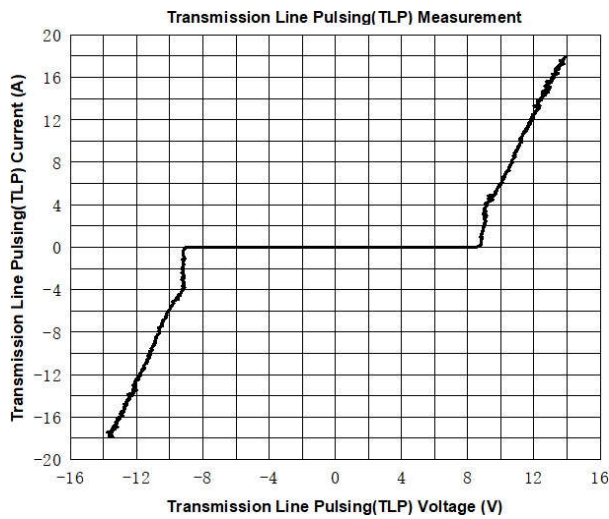
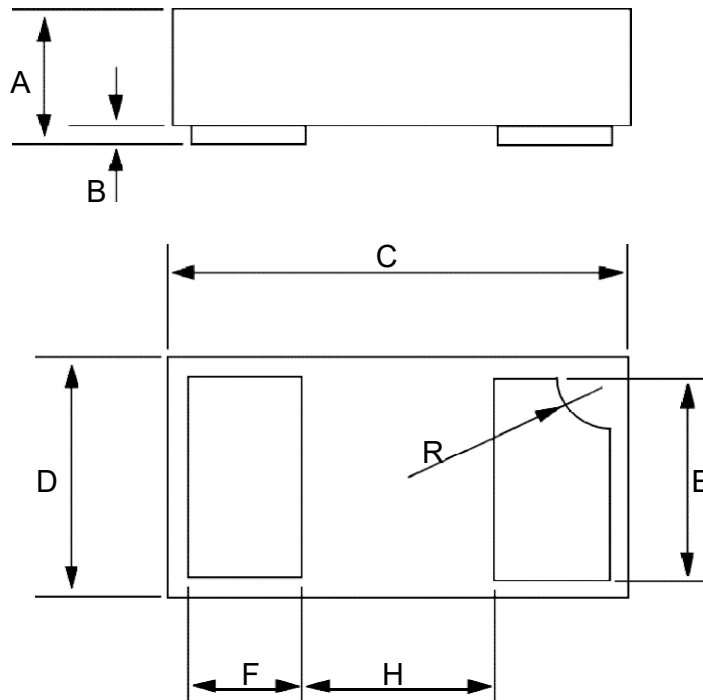


Fig2. ESD Clamping Voltage Screenshot Negative 8 kV Contact per IEC61000-4-2



Package Outline

DFN1006



Dim	Inches		Millimeters	
	MIN	MAX	MIN	MAX
A	0.013	0.015	0.34	0.40
B	0.000	0.002	0.00	0.05
C	0.037	0.042	0.95	1.075
D	0.021	0.026	0.55	0.675
E	0.017	0.021	0.45	0.55
F	0.007	0.011	0.20	0.30
H	0.015Typ.		0.40Typ.	
R	0.001	0.005	0.05	0.15

Summary of Packing Options

Package	Package Description	Packing Quantity	Industry Standard
DFN1006	Tape/Reel, 7" reel	10000	EIA-481-1